

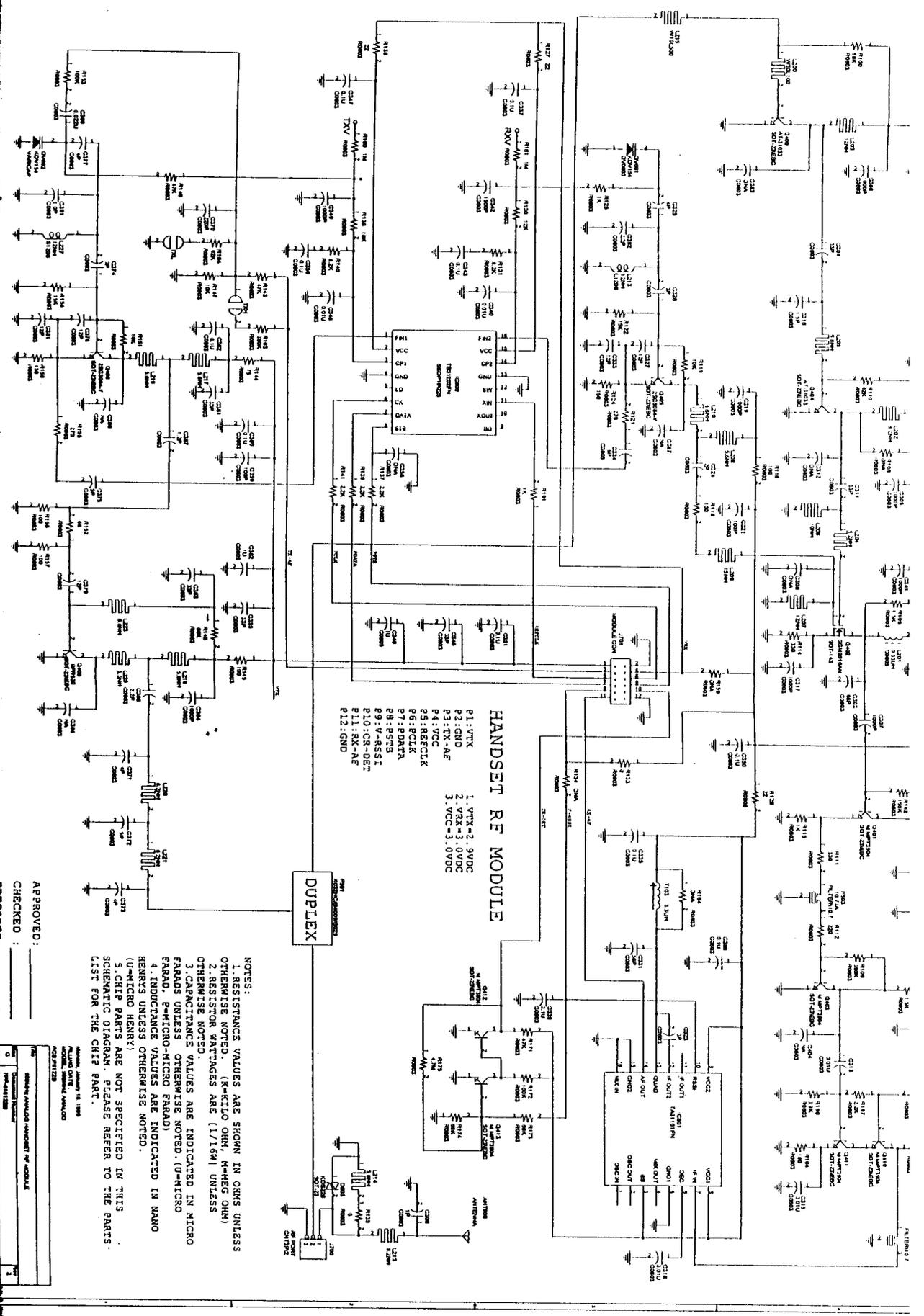
BASE RF MODULE

- 1. VTX=4.9VDC
 - 2. VRX=5.0VDC
 - 3. VCC=5.0VDC
- 81: VTX
 82: GND
 83: VTX-AF
 84: VCC
 85: RECLK
 86: DATA
 87: DATA
 88: CR-DET
 89: CR-DET
 90: CR-DET
 91: CR-DET
 92: GND

NOTES:
 1. RESISTANCE VALUES ARE SHOWN IN OHMS UNLESS OTHERWISE NOTED. (K=KILO OHM, M=MEG OHM)
 2. RESISTOR WATTAGES ARE [1/16W] UNLESS OTHERWISE NOTED.
 3. CAPACITANCE VALUES ARE INDICATED IN MICRO FARAD. P=PICO-FARAD
 4. INDUCTANCE VALUES ARE INDICATED IN NANO HENRY UNLESS OTHERWISE NOTED.
 5. CHIP PARTS ARE NOT SPECIFIED IN THIS SCHEMATIC DIAGRAM. PLEASE REFER TO THE PARTS LIST FOR THE CHIP PART.

APPROVED: _____
 CHECKED: _____
 PREPARED: _____

REVISION: January 28, 1988
 DRAWN: J. J. WILSON
 CHECKED: J. J. WILSON
 APPROVED: J. J. WILSON
 TITLE: BASE RF MODULE
 PART: PCEP1128



HANDSET RF MODULE

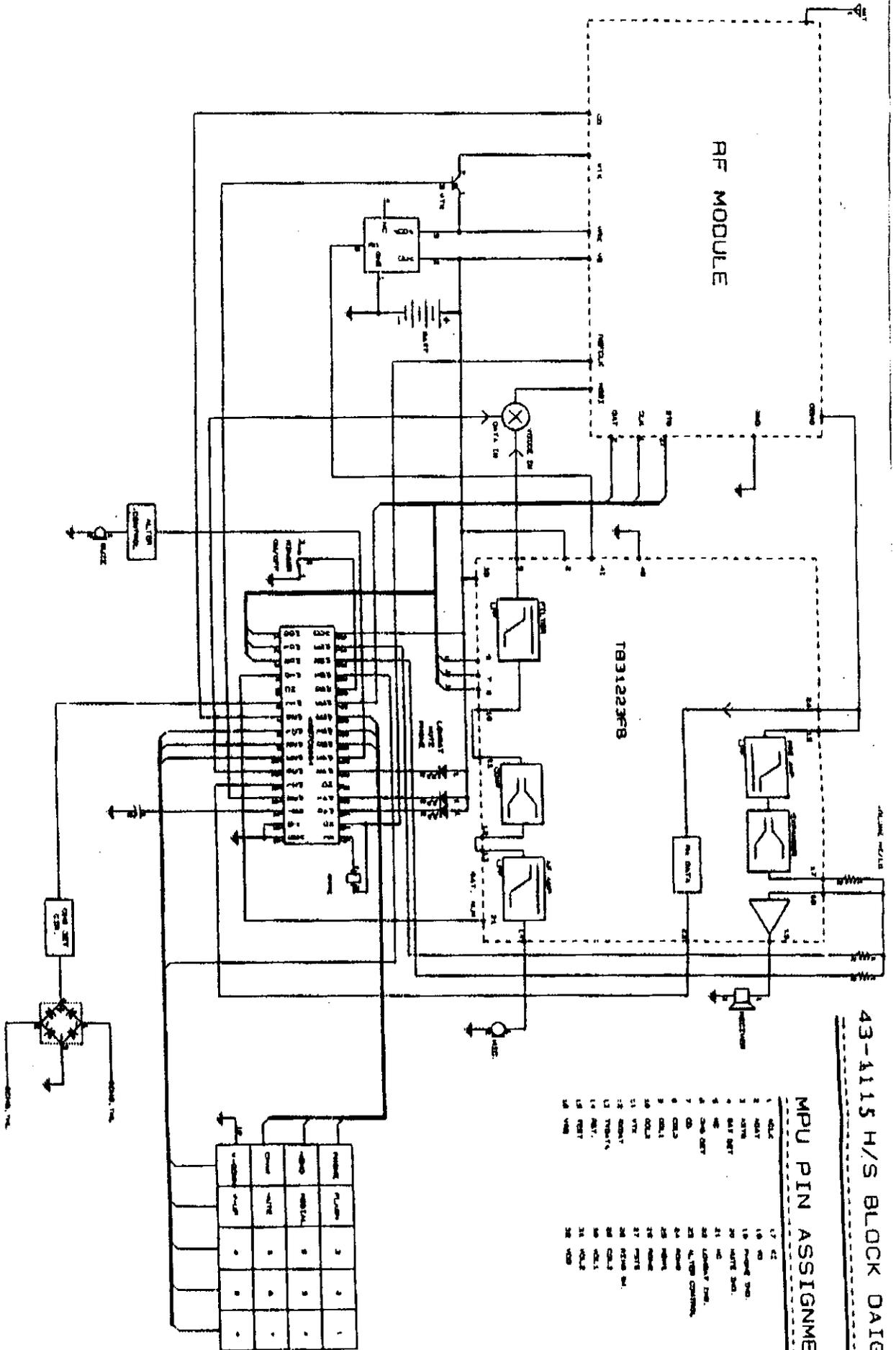
- P1: VTX
- P2: GND
- P3: VTX
- P4: VCC
- P5: REBCLK
- P6: RCLK
- P7: RDATA
- P8: RSTB
- P9: V-RSS1
- P10: CS-DET
- P11: RX-NF
- P12: GND

DUPLEX

NOTES:
 1. RESISTANCE VALUES ARE SHOWN IN OHMS UNLESS OTHERWISE NOTED. (K=KILO OHM, M=MEG OHM)
 2. RESISTOR TOLERANCES ARE (1/16W) UNLESS OTHERWISE NOTED.
 3. CAPACITANCE VALUES ARE INDICATED IN MICRO FARAD, P=PICTO-MICRO FARAD.
 4. INDUCTANCE VALUES ARE INDICATED IN NANO HENRY UNLESS OTHERWISE NOTED.
 5. CHIP PARTS ARE NOT SPECIFIED IN THIS SCHEMATIC DIAGRAM. PLEASE REFER TO THE PARTS LIST FOR THE CHIP PART.

APPROVED: _____
 CHECKED: _____

DATE	1998 JAN 14
DESIGNED BY	XXXXXXXXXX
CHECKED BY	XXXXXXXXXX
APPROVED BY	XXXXXXXXXX
REVISION	XXXXXXXXXX



RF MODULE

TB31223F8

MPU PIN ASSIGNMENT

1	VCC	17	CS
2	NC	18	RD
3	NC	19	WR
4	NC	20	RD
5	NC	21	WR
6	NC	22	RD
7	NC	23	WR
8	NC	24	RD
9	NC	25	WR
10	NC	26	RD
11	NC	27	WR
12	NC	28	RD
13	NC	29	WR
14	NC	30	RD
15	NC	31	WR
16	NC	32	RD

43-1115 H/S BLOCK DAIGRAM

APPROVED:

CHECKED:

PREPARED: